



ELECTRONICS INDUSTRY (USA) CO., LTD.

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BR5000 - BR5010

PRV : 50 - 1000 Volts

Io : 50 Amperes

FEATURES :

- * High case dielectric strength
- * High surge current capability
- * High reliability
- * High efficiency
- * Low reverse current
- * Low forward voltage drop

MECHANICAL DATA :

- * Case : Molded plastic with heatsink integrally mounted in the bridge encapsulation
- * Epoxy : UL94V-O rate flame retardant
- * Terminals : plated .25" (6.35 mm). Faston
- * Polarity : Polarity symbols marked on case
- * Mounting position : Bolt down on heat-sink with silicone thermal compound between bridge and mounting surface for maximum heat transfer efficiency.
- * Weight : 17.1 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

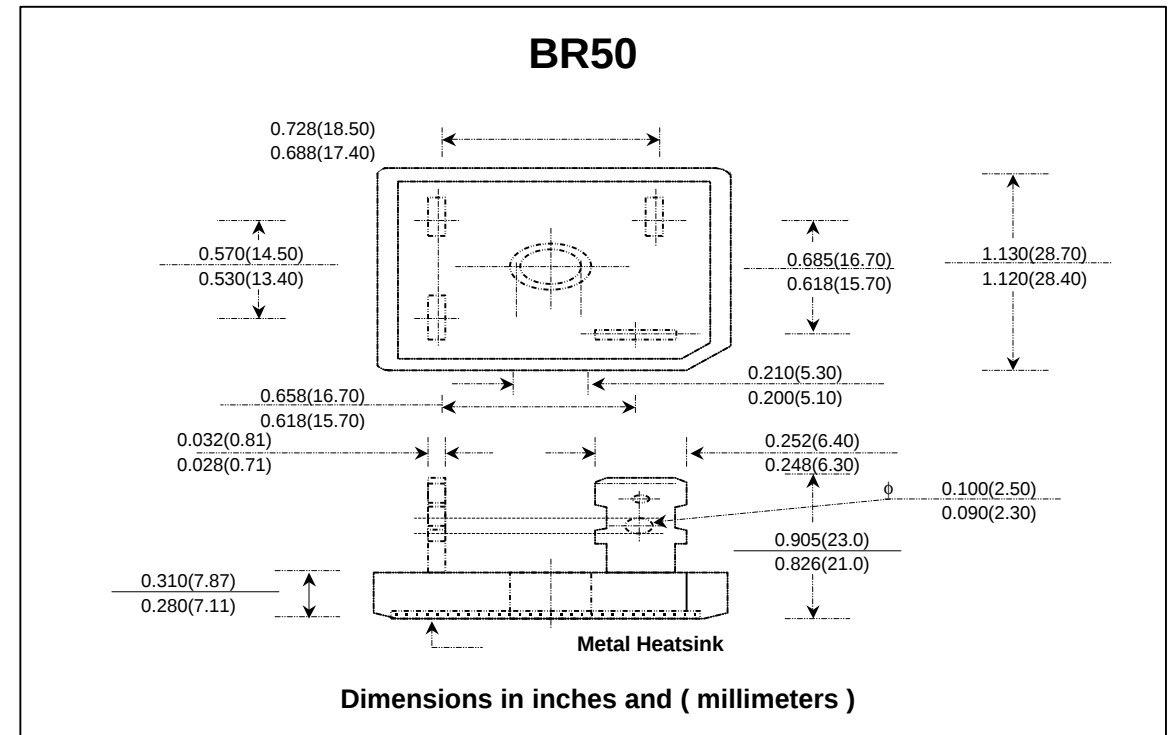
Rating at 25 °C ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

RATING	SYMBOL	BR5000	BR5001	BR5002	BR5004	BR5006	BR5008	BR5010	UNIT
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	Volts
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	Volts
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	Volts
Maximum Average Forward Current $T_c = 55^\circ C$	$I_{F(AV)}$	50							Amps.
Peak Forward Surge Current Single half sine wave Superimposed on rated load (JEDEC Method)	I_{FSM}	500							Amps.
Current Squared Time at $t < 8.3$ ms.	$I^2 t$	660							$A^2 S$
Maximum Forward Voltage per Diode at $I_F = 25$ Amp.	V_F	1.1							Volts
Maximum DC Reverse Current $T_a = 25^\circ C$ at Rated DC Blocking Voltage $T_a = 100^\circ C$	I_R	10							μA
	$I_{R(H)}$	200							μA
Typical Thermal Resistance (Note 1)	$R_{\theta JC}$	1.0							$^\circ C/W$
Operating Junction Temperature Range	T_J	- 40 to + 150							$^\circ C$
Storage Temperature Range	T_{STG}	- 40 to + 150							$^\circ C$

Notes :

- 1) Thermal resistance from Junction to Case with units mounted on a 9"x5"x4.6" (22.9x12.7x11.7 cm) Al-Finned Heatsink.

SILICON BRIDGE RECTIFIERS



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Certificate Number: Q10561



Certificate Number: E17276

RATING AND CHARACTERISTIC CURVES (BR5000 - BR5010)

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

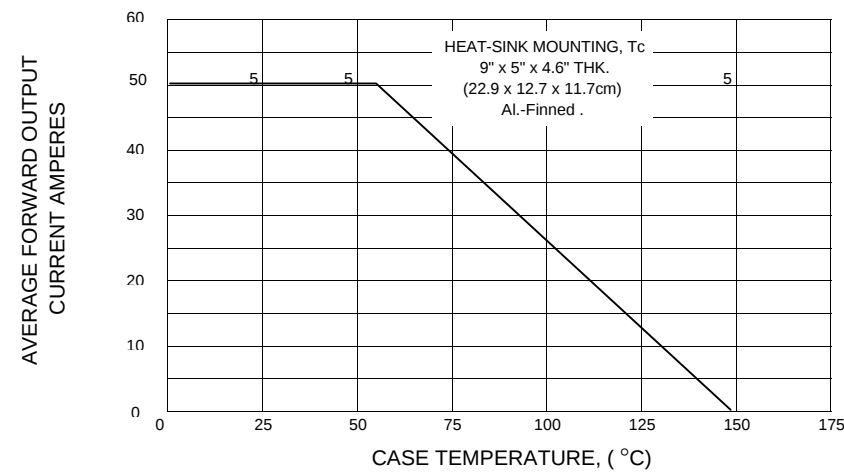


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

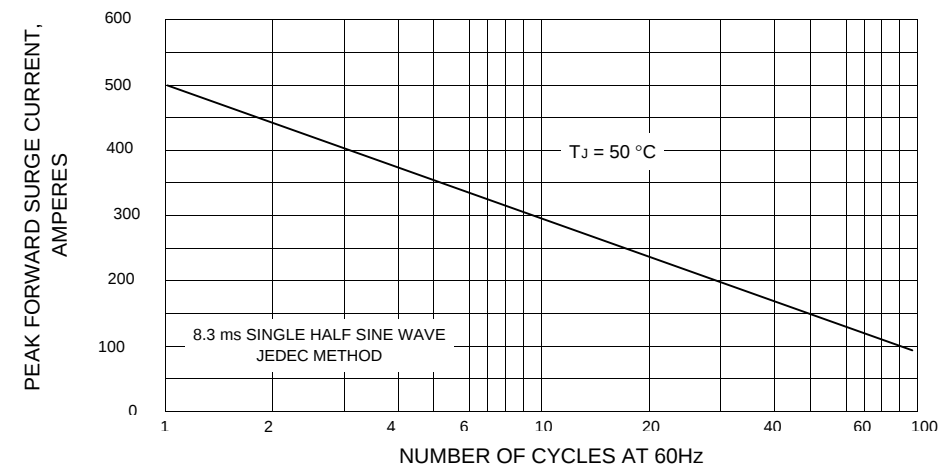


FIG.3 - TYPICAL FORWARD CHARACTERISTICS PER DIODE

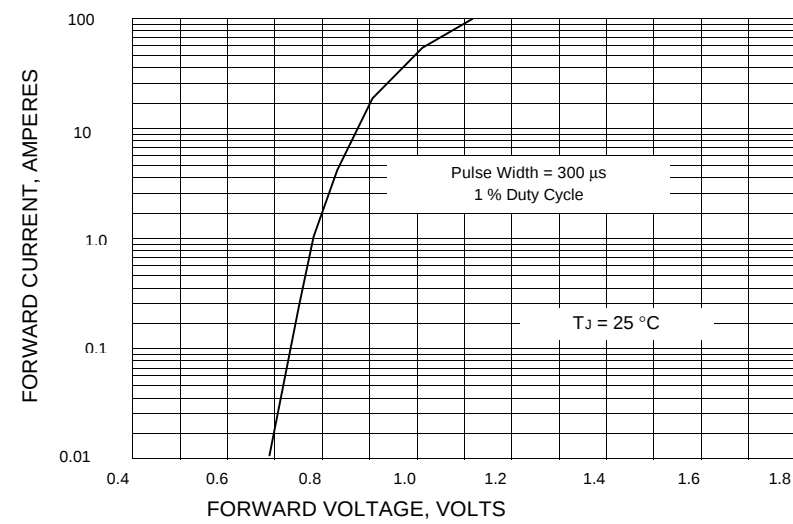


FIG.4 - TYPICAL REVERSE CHARACTERISTICS PER DIODE

